

ABSTRACT OF THE DISCLOSURE

A structure of a CMOS image sensory device is described. A photodiode sensory region and a transistor device region are isolated from each other by an isolation layer formed in the substrate. A gate structure is located on the transistor device region, and a source/drain region is in the transistor device region beside the side of the gate structure.
5 A doped region is in the photodiode sensory region. A self-aligned block is located on the photodiode sensory region and a protective layer is formed on the entire substrate.

09929544 - 09929545